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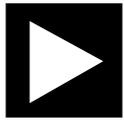
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GENERAL FEATURES

Wide supply voltage operation: 2.4 V to 3.7 V
 Internal bipolar switch between regulated and battery inputs
 Ultralow power operation with power saving modes (PSM)
 Full operation: 4.4 mA to 1.6 mA (PLL clock dependent)
 Battery mode: 3.3 mA to 400 μ A (PLL clock dependent)
 Sleep mode
 Real-time clock (RTC) mode: 1.7 μ A
 RTC and LCD mode: 38 μ A (LCD charge pump enabled)
 Reference: 1.2 V \pm 0.1% (10 ppm/ $^{\circ}$ C drift)
 64-lead, low profile quad flat, RoHS-compliant package (LQFP)
 Operating temperature range: -40° C to $+85^{\circ}$ C

ENERGY MEASUREMENT FEATURES

Proprietary analog-to-digital converters (ADCs) and digital signal processing (DSP) provide high accuracy active (watt), reactive (var), and apparent energy (volt-ampere (VA)) measurement
 <0.1% error on active energy over a dynamic range of 1000 to 1 @ 25° C
 <0.5% error on reactive energy over a dynamic range of 1000 to 1 @ 25° C (ADE5169 and ADE5569 only)
 <0.5% error on root mean square (rms) measurements over a dynamic range of 500 to 1 for current (I_{rms}) and 100 to 1 for voltage (V_{rms}) @ 25° C
 Supports IEC 62053-21; IEC 62053-22; IEC 62053-23; EN 50470-3 Class A, Class B, and Class C; and ANSI C12-16
 Differential input with programmable gain amplifiers (PGAs) supports shunts, current transformers, and di/dt current sensors (ADE5169 and ADE5569 only)
 2 current inputs for antitamper detection in the ADE5166/ADE5169
 High frequency outputs proportional to I_{rms} , active, reactive, or apparent power (AP)

Table 1. Features Available on Each Part

Part No.	Antitamper	Watt, VA, I_{rms} , V_{rms}	Var	di/dt Sensor	Memory Size
ADE5166	Yes	Yes	No	No	62kB
ADE5169	Yes	Yes	Yes	Yes	32kB or 62kB
ADE5566	No	Yes	No	No	62kB
ADE5569	No	Yes	Yes	Yes	62kB

MICROPROCESSOR FEATURES

8052-based core
 Single-cycle 4 MIPS 8052 core
 8052-compatible instruction set
 32.768 kHz external crystal with on-chip PLL
 2 external interrupt sources
 External reset pin
 Low power battery mode
 Wake-up from I/O, temperature change, alarm, and universal asynchronous receiver/transmitter (UART)
 LCD driver operation with automatic scrolling
 Temperature measurement
 Real-time clock (RTC)
 Counter for seconds, minutes, hours, days, months, and years
 Date counter, including leap year compensation
 Automatic battery switchover for RTC backup
 Operation down to 2.4 V
 Ultralow battery supply current: 1.7 μ A
 Selectable output frequency: 1 Hz to 16 kHz
 Embedded digital crystal frequency compensation for calibration and temperature variation of 2 ppm resolution
 Integrated LCD driver
 108-segment driver for the ADE5566 and ADE5569
 104-segment driver for the ADE5166 and ADE5169
 2 \times , 3 \times , or 4 \times multiplexing
 4 LCD memory banks for screen scrolling
 LCD voltages generated internally or with external resistors
 Internal adjustable drive voltages up to 5 V independent of power supply level
 On-chip peripherals
 2 independent UART interfaces
 SPI or I²C
 Watchdog timer
 Power supply management with user-selectable levels
 Memory: 62 kB flash memory, 2.256 kB RAM
 Development tools
 Single-pin emulation
 IDE-based assembly and C source debugging

Rev. D

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4/12—Rev. C to Rev. D

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6/10—Rev. B to Rev. C

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11/09—Rev. A to Rev. B

Deleted RTCCAL Function Throughout

Changes to Fault Detection (ADE5166/ADE5169 Only) Section 51

2/09—Rev. 0 to Rev. A

Added ADE5566/ADE5569 Universal

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10/08—Revision 0: Initial Version

GENERAL DESCRIPTION

The ADE5166/ADE5169/ADE5566/ADE5569¹ integrate the Analog Devices, Inc., energy (ADE) metering IC analog front end and fixed function DSP solution with an enhanced 8052 MCU core, a full RTC, an LCD driver, and all the peripherals to make an electronic energy meter with an LCD display in a single part.

The ADE measurement core includes active, reactive, and apparent energy calculations, as well as voltage and current rms measurements. This information is accessible for energy billing by using the built-in energy scalars. Many power line supervisory features such as SAG, peak, and zero crossing are included in the energy measurement DSP to simplify energy meter design.

The microprocessor functionality includes a single-cycle 8052 core, a full RTC with a power supply backup pin, an SPI or I²C interface, and two independent UART interfaces. The ready-to-use information from the ADE core reduces the requirement for program memory size, making it easy to integrate complicated design into 62 kB of flash memory.

¹ Patents pending.

The ADE5166/ADE5169 include a 104-segment LCD driver and the ADE5566/ADE5569 include a 108-segment LCD driver, each with the capability to store up to four LCD screens in memory. This driver generates voltages capable of driving LCDs up to 5 V.

32 KB FLASH OPTION

A reduced memory version of the ADE5169 is available with 32 kB of flash memory. A description of the flash memory organization of this model is provided in the Flash Memory Organization for the 32 kB Model section. All other features and functionality are identical between the models and no reference is made in the remainder of this data sheet to the 32 kB model. If using the 32 kB model, 62 kB should therefore be substituted in any references to 62 kB of flash memory.

FUNCTIONAL BLOCK DIAGRAMS

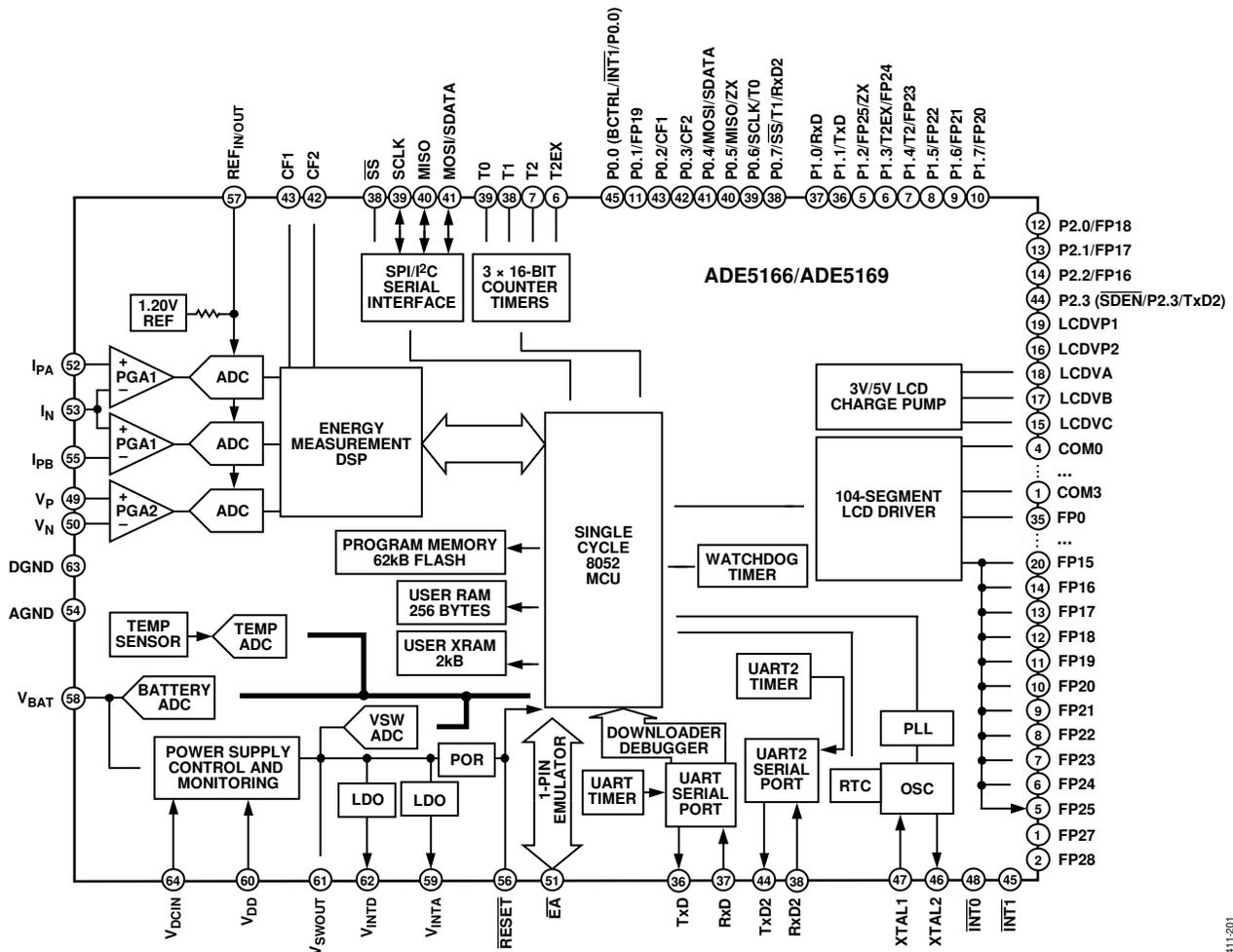


Figure 1. ADE5166/ADE5169 Functional Block Diagram

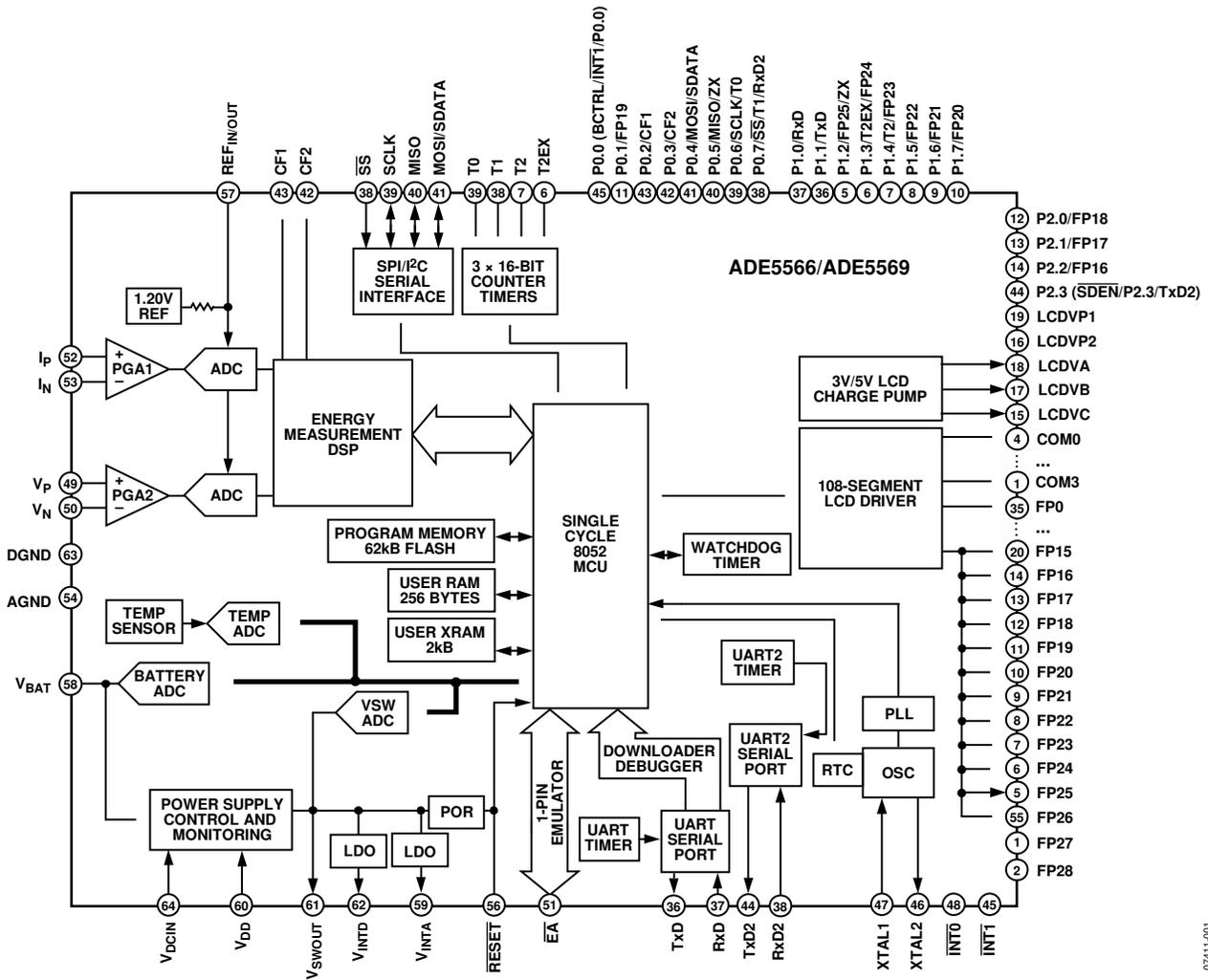


Figure 2. ADE5566/ADE5569 Functional Block Diagram

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SPECIFICATIONS

$V_{DD} = 3.3\text{ V} \pm 5\%$, $AGND = DGND = 0\text{ V}$, on-chip reference $XTALX = 32.768\text{ kHz}$, T_{MIN} to $T_{MAX} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, unless otherwise noted.

ENERGY METERING

Table 2.

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
MEASUREMENT ACCURACY¹					
Phase Error Between Channels					
PF = 0.8 Capacitive		±0.05		Degrees	Phase lead: 37°
PF = 0.5 Inductive		±0.05		Degrees	Phase lag: 60°
Active Energy Measurement Error ²		0.1		% of reading	Over a dynamic range of 1000 to 1 at 25°C
AC Power Supply Rejection ²					$V_{DD} = 3.3\text{ V} + 100\text{ mV rms}/120\text{ Hz}$
Output Frequency Variation		0.01		%	$I_{Px} = V_P = \pm 100\text{ mV rms}$
DC Power Supply Rejection ²					$V_{DD} = 3.3\text{ V} \pm 117\text{ mV dc}$
Output Frequency Variation		0.01		%	
Active Energy Measurement Bandwidth ¹		8		kHz	
Reactive Energy Measurement Error ²		0.5		% of reading	Over a dynamic range of 1000 to 1 at 25°C
V_{rms} Measurement Error ²		0.5		% of reading	Over a dynamic range of 100 to 1 at 25°C
V_{rms} Measurement Bandwidth ¹		63.7		Hz	Fundamental only, mean absolute measurement
I_{rms} Measurement Error ²		0.5		% of reading	Over a dynamic range of 500 to 1 at 25°C
I_{rms} Measurement Bandwidth ¹		3.9		kHz	
ANALOG INPUTS					
Maximum Signal Levels			±500	mV peak	$V_P - V_N$ differential input
ADE5166/ADE5169			±500	mV peak	$I_{PA} - I_N$ and $I_{PB} - I_N$ differential inputs
ADE5566/ADE5569			±500	mV peak	$I_P - I_N$
Input Impedance (DC)		770		k Ω	
ADC Offset Error ²		±10		mV	PGA1 = PGA2 = 1
		±1		mV	PGA1 = 16
Gain Error ²					
Current Channel		±3		%	$I_{PA} = I_{PB} = 0.5\text{ V dc}$ or $I_P = 0.5\text{ V dc}$
Voltage Channel		±3		%	$V_P - V_N = 0.5\text{ V dc}$
Gain Error Match		±0.2		%	
CF1 AND CF2 PULSE OUTPUT					
Maximum Output Frequency		21.6		kHz	$V_P - V_N = 500\text{ mV peak}$; $I_{PA} - I_N = 500\text{ mV}$ for the ADE5166/ADE5169; $I_P - I_N = 500\text{ mV}$ for the ADE5566/ADE5569
Duty Cycle		50		%	If the CF1 or CF2 frequency > 5.55 Hz
Active High Pulse Width		90		ms	If the CF1 or CF2 frequency < 5.55 Hz
FAULT DETECTION³					
Fault Detection Threshold					
Inactive Input \neq Active Input		6.25		% of active	I_{PA} or I_{PB} active
Input Swap Threshold					
Inactive Input > Active Input		6.25		% of active	I_{PA} or I_{PB} active
Accuracy Fault Mode Operation					
I_{PA} Active, $I_{PB} = AGND$		0.1		% of reading	Over a dynamic range of 500 to 1
I_{PB} Active, $I_{PA} = AGND$		0.1		% of reading	Over a dynamic range of 500 to 1
Fault Detection Delay		3		Seconds	
Swap Delay		3		Seconds	

¹ These specifications are not production tested but are guaranteed by design and/or characterization data on production release.

² See the Terminology section for definition.

³ Available only in the ADE5166/ADE5169.

ANALOG PERIPHERALS

Table 3.

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments	
INTERNAL ADCs (BATTERY, TEMPERATURE, V_{DCIN})						
Power Supply Operating Range	2.4		3.7	V	Measured on V _{SWOUT}	
No Missing Codes ¹	8			Bits		
Conversion Delay ²		38		μs		
ADC Gain						
V _{DCIN} Measurement		15.3		mV/LSB		
V _{BAT} Measurement		14.6		mV/LSB		
Temperature Measurement		0.83		°C/LSB		
ADC Offset						
V _{DCIN} Measurement at 3 V		200		LSB		
V _{BAT} Measurement at 3.7 V		246		LSB		
Temperature Measurement at 25°C		123		LSB		
V_{DCIN} Analog Input						
Maximum Signal Levels	0		3.3	V		
Input Impedance (DC)	1			MΩ		
Low V _{DCIN} Detection Threshold	1.09	1.2	1.27	V		
POWER-ON RESET (POR)						
V_{DD} POR						
Detection Threshold	2.5		2.95	V		
POR Active Timeout Period		33		ms		
V_{SWOUT} POR						
Detection Threshold	1.8		2.2	V		
POR Active Timeout Period		20		ms		
V_{INTD} POR						
Detection Threshold	2.0		2.25	V		
POR Active Timeout Period		16		ms		
V_{INTA} POR						
Detection Threshold	2.0		2.25	V		
POR Active Timeout Period		120		ms		
BATTERY SWITCHOVER						
Voltage Operating Range (V _{SWOUT})	2.4		3.7	V	When V _{DD} to V _{BAT} switch is activated by V _{DD} When V _{DD} to V _{BAT} switch is activated by V _{DCIN}	
V_{DD} to V_{BAT} Switching						
Switching Threshold (V _{DD})	2.5		2.95	V		
Switching Delay		10		ns		
		30		ms		
V_{BAT} to V_{DD} Switching						
Switching Threshold (V _{DD})	2.5		2.95	V		
Switching Delay		30		ms		
V _{SWOUT} to V _{BAT} Leakage Current		10		nA	Based on V _{DD} > 2.75 V V _{BAT} = 0 V, V _{SWOUT} = 3.43 V, T _A = 25°C	
LCD, CHARGE PUMP ACTIVE						
Charge Pump Capacitance Between LCDVP1 and LCDVP2	100			nF		
LCDVA, LCDVB, LCDVC Decoupling Capacitance						
LCDVA	0		1.9	V	1/3 bias mode	
LCDVB	0		3.8	V		
LCDVC	0		5.8	V		
V1 Segment Line Voltage	LCDVA – 0.1		LCDVA	V	Current on segment line = –2 μA	
V2 Segment Line Voltage	LCDVB – 0.1		LCDVB	V	Current on segment line = –2 μA	
V3 Segment Line Voltage	LCDVC – 0.1		LCDVC	V	Current on segment line = –2 μA	
DC Voltage Across Segment and COMx Pin			50	mV	LCDVC – LCDVB, LCDVC – LCDVA, or LCDVB – LCDVA	

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
LCD, RESISTOR LADDER ACTIVE					
Leakage Current		±20		nA	1/2 and 1/3 bias modes, no load
V1 Segment Line Voltage	LCDVA – 0.1		LCDVA	V	Current on segment line = –2 µA
V2 Segment Line Voltage	LCDVB – 0.1		LCDVB	V	Current on segment line = –2 µA
V3 Segment Line Voltage	LCDVC – 0.1		LCDVC	V	Current on segment line = –2 µA
ON-CHIP REFERENCE					Nominal 1.2035 V
Reference Error	–2.2		+2.2	mV	T _A = 25°C, f _{CORE} = 1.024 MHz
Power Supply Rejection		80		dB	
Temperature Coefficient ¹		10	50	ppm/°C	f _{CORE} = 1.024 MHz

¹ These specifications are not production tested but are guaranteed by design and/or characterization data on production release.

² Delay between ADC conversion request and interrupt set.

DIGITAL INTERFACE

Table 4.

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
LOGIC INPUTS ¹					
All Inputs Except XTAL1, XTAL2, BCTRL, INT0, INT1, RESET					
Input High Voltage, V _{INH}	2.0			V	
Input Low Voltage, V _{INL}			0.8	V	
BCTRL, INT0, INT1, RESET					
Input High Voltage, V _{INH}	1.3			V	
Input Low Voltage, V _{INL}			0.8	V	
Input Currents					
RESET			100	nA	RESET = V _{SWOUT} = 3.3 V
Port 0, Port 1, Port 2			±100	nA	Internal pull-up disabled, input = 0 V or V _{SWOUT}
	–3.75		–8.5	µA	Internal pull-up enabled, input = 0 V, V _{SWOUT} = 3.3 V
Input Capacitance		10		pF	All digital inputs
FLASH MEMORY					
Endurance ²	20,000			Cycles	At 25°C
Data Retention ³	20			Years	T _J = 85°C
CRYSTAL OSCILLATOR ⁴					
Crystal Equivalent Series Resistance	30		50	kΩ	
Crystal Frequency	32	32.768	33.5	kHz	
XTAL1 Input Capacitance		12		pF	
XTAL2 Output Capacitance		12		pF	
MCU CLOCK RATE (f _{CORE})		4.096		MHz	Crystal = 32.768 kHz and CD bits = 0b000
		32		kHz	Crystal = 32.768 kHz and CD bits = 0b111
LOGIC OUTPUTS					
Output High Voltage, V _{OH}	2.4			V	V _{DD} = 3.3 V ± 5%
I _{SOURCE}			80	µA	
Output Low Voltage, V _{OL} ⁵			0.4	V	V _{DD} = 3.3 V ± 5%
I _{SINK}			2	mA	
START-UP TIME ⁶					
PSM0 Power-On Time		880		ms	V _{DD} at 2.75 V to PSM0 code execution
From Power Saving Mode 1 (PSM1)					
PSM1 to PSM0		130		ms	V _{DD} at 2.75 V to PSM0 code execution
From Power Saving Mode 2 (PSM2)					
PSM2 to PSM1		48		ms	Wake-up event to PSM1 code execution
PSM2 to PSM0		186		ms	V _{DD} at 2.75 V to PSM0 code execution

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
POWER SUPPLY INPUTS					
V _{DD}	3.13	3.3	3.46	V	
V _{BAT}	2.4	3.3	3.7	V	
INTERNAL POWER SUPPLY SWITCH (V_{SWOUT})					
V _{BAT} to V _{SWOUT} On Resistance			12	Ω	V _{BAT} = 2.4 V
V _{DD} to V _{SWOUT} On Resistance			9	Ω	V _{DD} = 3.13 V
V _{BAT} to/from V _{DD} Switching Open Time		40		ns	
BCTRL State Change and Switch Delay		18		μs	
V _{SWOUT} Output Current Drive			6	mA	
POWER SUPPLY OUTPUTS					
V _{INTA}	2.3		2.70	V	
V _{INTD}	2.3		2.70	V	
V _{INTA} Power Supply Rejection		60		dB	
V _{INTD} Power Supply Rejection		50		dB	
POWER SUPPLY CURRENTS					
Current in Normal Mode (PSM0)		4.4	5.3	mA	f _{CORE} = 4.096 MHz, LCD and meter active
		2.2		mA	f _{CORE} = 1.024 MHz, LCD and meter active
		1.6		mA	f _{CORE} = 32.768 kHz, LCD and meter active
		3	3.9	mA	f _{CORE} = 4.096 MHz; metering ADC and DSP, powered down
Current in Battery Mode (PSM1)		3.3	5.05	mA	f _{CORE} = 4.096 MHz, LCD active, V _{BAT} = 3.7 V
		1		mA	f _{CORE} = 1.024 MHz, LCD active
Current in Sleep Mode (PSM2)		38		μA	LCD active with charge pump at 3.3 V + RTC, V _{BAT} = 3.3 V
		1.7		μA	RTC only, T _A = 25°C, V _{BAT} = 3.3 V

¹ Specifications guaranteed by design.

² Endurance is qualified as per JEDEC Standard 22 Method A117 and measured at -40°C, +25°C, +85°C, and +125°C.

³ Retention lifetime equivalent at junction temperature (T_j) = 85°C as per JEDEC Standard 22 Method A117. Retention lifetime derates with junction temperature.

⁴ Recommended crystal specifications.

⁵ Test carried out with all the I/Os set to a low output level.

⁶ Delay between power supply valid and execution of first instruction by 8052 core.

TIMING SPECIFICATIONS

AC inputs during testing were driven at $V_{SWOUT} - 0.5\text{ V}$ for Logic 1 and at 0.45 V for Logic 0. Timing measurements were made at V_{IH} minimum for Logic 1 and at V_{IL} maximum for Logic 0, as shown in Figure 3.

For timing purposes, a port pin is no longer floating when a 100 mV change from load voltage occurs. A port pin begins to float when a 100 mV change from the loaded V_{OH}/V_{OL} level occurs, as shown in Figure 3.

$C_{LOAD} = 80\text{ pF}$ for all outputs, unless otherwise noted. $V_{DD} = 2.7\text{ V}$ to 3.6 V ; all specifications T_{MIN} to T_{MAX} , unless otherwise noted.

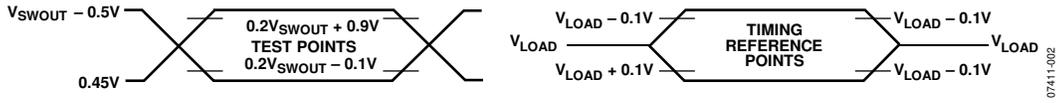


Figure 3. Timing Waveform Characteristics

Table 5. Clock Input (External Clock Driven XTAL1) Parameters

Parameter	Description	32.768 kHz External Crystal			Unit
		Min	Typ	Max	
t_{CK}	XTAL1 period		30.52		μs
t_{CKL}	XTAL1 width low		6.26		μs
t_{CKH}	XTAL1 width high		6.26		μs
t_{CKR}	XTAL1 rise time		9		ns
t_{CKF}	XTAL1 fall time		9		ns
$1/t_{CORE}$	Core clock frequency ¹		1.024		MHz

¹ The ADE5166/ADE5169/ADE5566/ADE5569 internal PLL locks onto a multiple (512x) of the 32.768 kHz external crystal frequency to provide a stable 4.096 MHz internal clock for the system. The core can operate at this frequency or at a binary submultiple defined by the CD bits of the POWCON SFR, Address 0xC5[2:0] (see Table 26).

Table 6. I²C-Compatible Interface Timing Parameters (400 kHz)

Parameter	Description	Typ	Unit
t_{BUF}	Bus-free time between stop condition and start condition	1.3	μs
t_L	SCLK low pulse width	1.36	μs
t_H	SCLK high pulse width	1.14	μs
t_{SHD}	Start condition hold time	251.35	μs
t_{DSU}	Data setup time	740	ns
t_{DHD}	Data hold time	400	ns
t_{RSU}	Setup time for repeated start	12.5	ns
t_{PSU}	Stop condition setup time	400	ns
t_R	Rise time of both SCLK and SDATA	200	ns
t_F	Fall time of both SCLK and SDATA	300	ns
t_{SUP}^1	Pulse width of spike suppressed	50	ns

¹ Input filtering on both the SCLK and SDATA suppresses noise spikes of $<50\text{ ns}$.

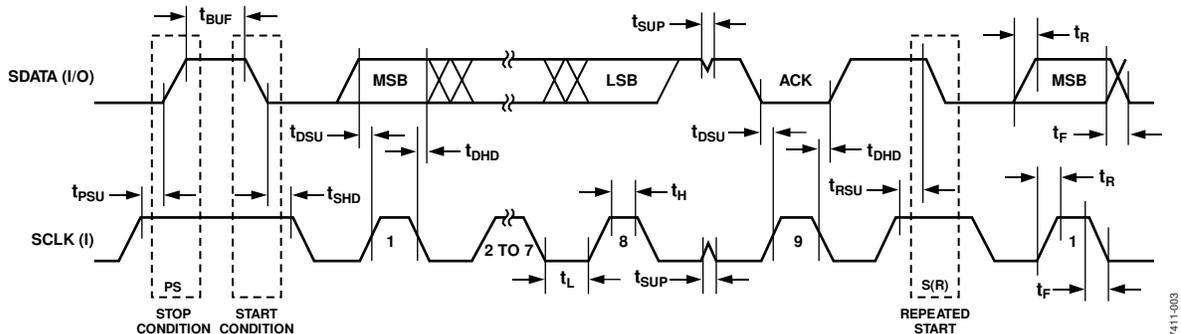


Figure 4. I²C-Compatible Interface Timing

Table 7. SPI Master Mode Timing Parameters (SPICPHA = 1)

Parameter	Description	Min	Typ	Max	Unit
t _{SL}	SCLK low pulse width	2 ^{SPIR} × t _{CORE} ¹			ns
t _{SH}	SCLK high pulse width	2 ^{SPIR} × t _{CORE} ¹			ns
t _{DAV}	Data output valid after SCLK edge			3 × t _{CORE} ¹	ns
t _{DSU}	Data input setup time before SCLK edge	0			ns
t _{DHD}	Data input hold time after SCLK edge	t _{CORE} ¹			ns
t _{DF}	Data output fall time		19		ns
t _{DR}	Data output rise time		19		ns
t _{SR}	SCLK rise time		19		ns
t _{SF}	SCLK fall time		19		ns

¹ t_{CORE} depends on the clock divider or the CD bits of the POWCON SFR, Address 0xC5[2:0] (see Table 26); t_{CORE} = 2^{CD}/4.096 MHz.

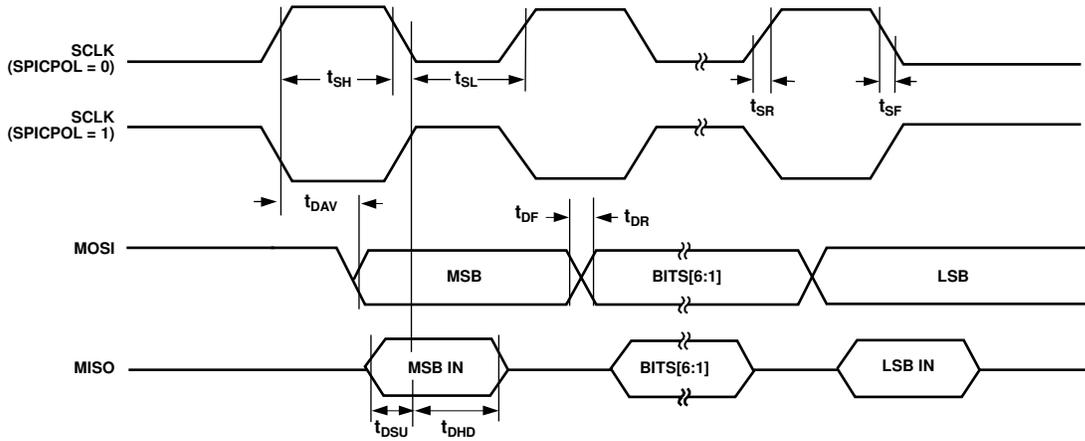


Figure 5. SPI Master Mode Timing (SPICPHA = 1)

07411-004

Table 8. SPI Master Mode Timing Parameters (SPICPHA = 0)

Parameter	Description	Min	Typ	Max	Unit
t _{SL}	SCLK low pulse width	$2^{SPIR} \times t_{CORE}^1$	$(SPIR + 1) \times t_{CORE}^1$		ns
t _{SH}	SCLK high pulse width	$2^{SPIR} \times t_{CORE}^1$	$(SPIR + 1) \times t_{CORE}^1$		ns
t _{DAV}	Data output valid after SCLK edge			$3 \times t_{CORE}^1$	ns
t _{DOSU}	Data output setup before SCLK edge			75	ns
t _{DSU}	Data input setup time before SCLK edge	0			ns
t _{DHD}	Data input hold time after SCLK edge	t_{CORE}^1			ns
t _{DF}	Data output fall time		19		ns
t _{DR}	Data output rise time		19		ns
t _{SR}	SCLK rise time		19		ns
t _{SF}	SCLK fall time		19		ns

¹ t_{CORE} depends on the clock divider or the CD bits of the POWCON SFR, Address 0xC5[2:0] (see Table 26); t_{CORE} = 2^{CD}/4.096 MHz.

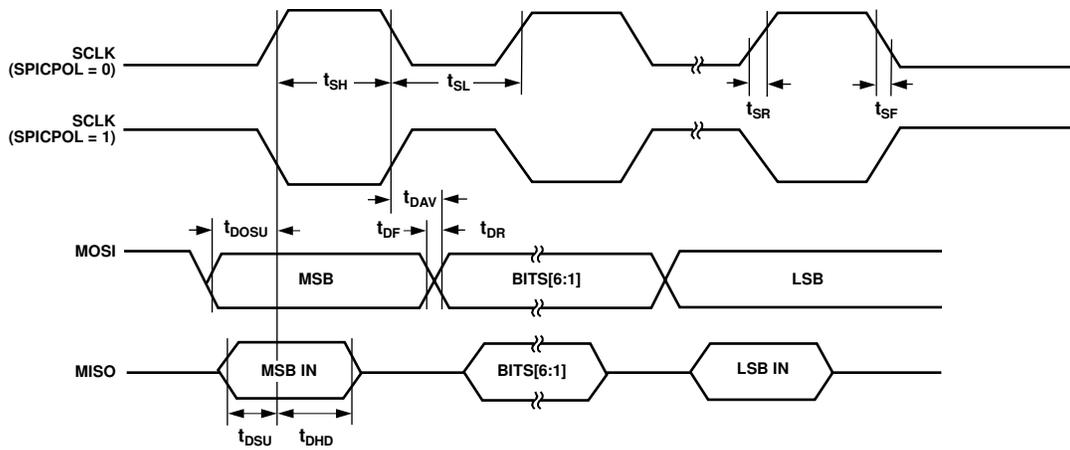


Figure 6. SPI Master Mode Timing (SPICPHA = 0)

07411-005

Table 9. SPI Slave Mode Timing Parameters (SPICPHA = 1)

Parameter	Description	Min	Typ	Max	Unit
$t_{\overline{SS}}$	\overline{SS} to SCLK edge	145			ns
t_{SL}	SCLK low pulse width	$6 \times t_{CORE}^1$			ns
t_{SH}	SCLK high pulse width	$6 \times t_{CORE}^1$			ns
t_{DAV}	Data output valid after SCLK edge			25	ns
t_{DSU}	Data input setup time before SCLK edge	0			ns
t_{DHD}	Data input hold time after SCLK edge	$2 \times t_{CORE}^1 + 0.5$			μ s
t_{DF}	Data output fall time		19		ns
t_{DR}	Data output rise time		19		ns
t_{SR}	SCLK rise time		19		ns
t_{SF}	SCLK fall time		19		ns
t_{SFS}	\overline{SS} high after SCLK edge	0			ns

¹ t_{CORE} depends on the clock divider or the CD bits of the POWCON SFR, Address 0xC5[2:0] (see Table 26); $t_{CORE} = 2^{CD}/4.096$ MHz.

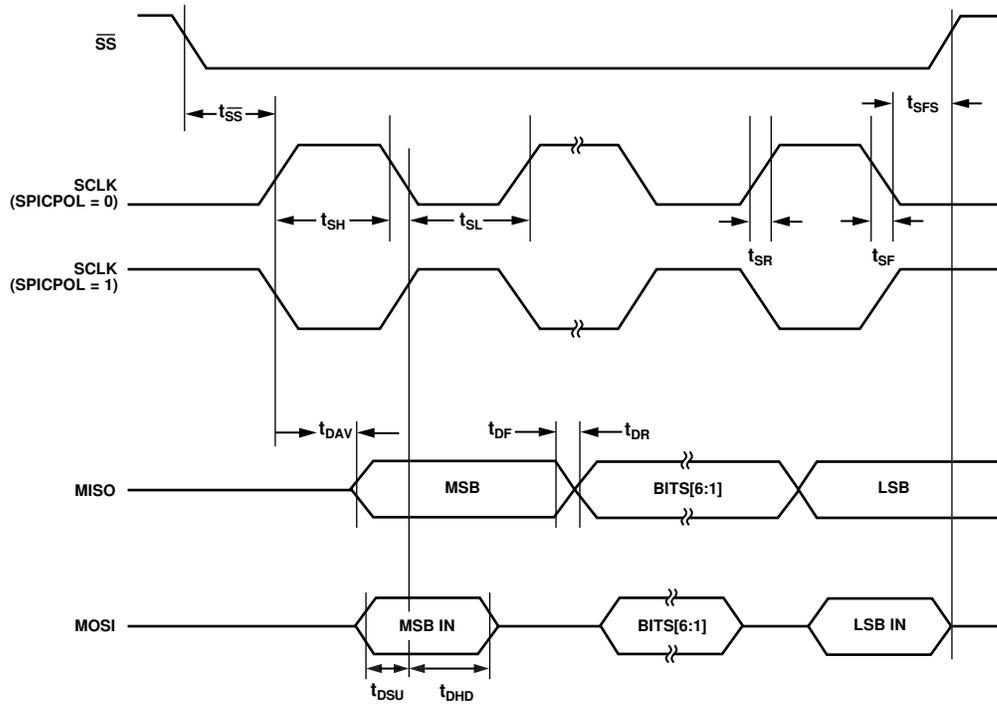


Figure 7. SPI Slave Mode Timing (SPICPHA = 1)

07411-006

Table 10. SPI Slave Mode Timing Parameters (SPICPHA = 0)

Parameter	Description	Min	Typ	Max	Unit
$t_{\overline{SS}}$	\overline{SS} to SCLK edge	145			ns
t_{SL}	SCLK low pulse width	$6 \times t_{CORE}^1$			ns
t_{SH}	SCLK high pulse width	$6 \times t_{CORE}^1$			ns
t_{DAV}	Data output valid after SCLK edge			25	ns
t_{DSU}	Data input setup time before SCLK edge	0			ns
t_{DHD}	Data input hold time after SCLK edge	$2 \times t_{CORE}^1 + 0.5$			μ s
t_{DF}	Data output fall time		19		ns
t_{DR}	Data output rise time		19		ns
t_{SR}	SCLK rise time		19		ns
t_{SF}	SCLK fall time		19		ns
t_{DOSS}	Data output valid after \overline{SS} edge	0			ns
t_{SFS}	\overline{SS} high after SCLK edge	0			ns

¹ t_{CORE} depends on the clock divider or the CD bits of the POWCON SFR, Address 0xC5[2:0] (see Table 26); $t_{CORE} = 2^{CD}/4.096$ MHz.

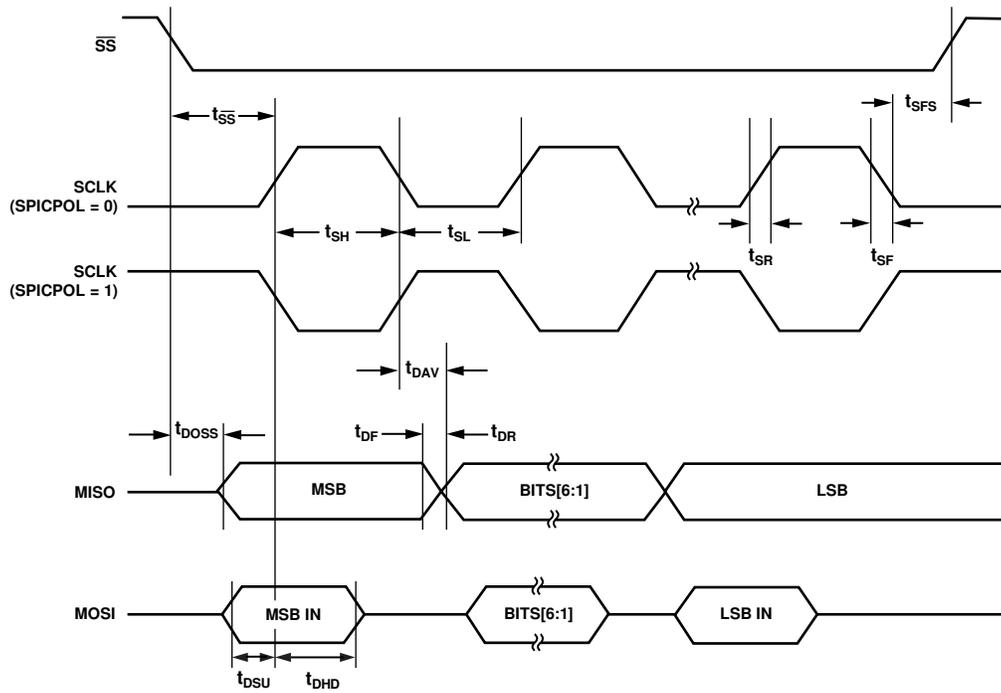


Figure 8. SPI Slave Mode Timing (SPICPHA = 0)

07411-007

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted.

Table 11.

Parameter	Rating
V _{DD} to DGND	−0.3 V to +3.7 V
V _{BAT} to DGND	−0.3 V to +3.7 V
V _{DCIN} to DGND	−0.3 V to V _{SWOUT} + 0.3 V
Input LCD Voltage to AGND, LCDVA, LCDVB, LCDVC ¹	−0.3 V to V _{SWOUT} + 0.3 V
Analog Input Voltage to AGND, V _P , V _N , I _P /I _{PA} , I _{PB} , and I _N	−2 V to +2 V
Digital Input Voltage to DGND	−0.3 V to V _{SWOUT} + 0.3 V
Digital Output Voltage to DGND	−0.3 V to V _{SWOUT} + 0.3 V
Operating Temperature Range (Industrial)	−40°C to +85°C
Storage Temperature Range	−65°C to +150°C
64-Lead LQFP, Power Dissipation Lead Temperature (Soldering, 30 sec)	300°C

¹ When used with external resistor divider.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case condition, that is, a device soldered in a circuit board for surface-mount packages.

Table 12. Thermal Resistance

Package Type	θ _{JA}	θ _{JC}	Unit
64-Lead LQFP	60	20.5	°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

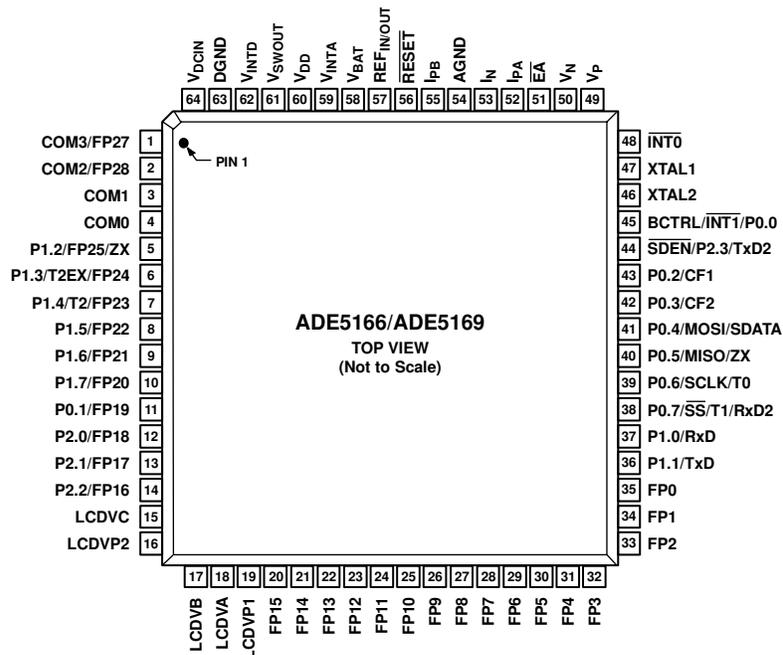


Figure 9. ADE5166/ADE5169 Pin Configuration

07411-010

Table 13. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	COM3/FP27	Common Output 3/LCD Segment Output 27. COM3 is used for the LCD backplane.
2	COM2/FP28	Common Output 2/LCD Segment Output 28. COM2 is used for the LCD backplane.
3	COM1	Common Output 1. COM1 is used for the LCD backplane.
4	COM0	Common Output 0. COM0 is used for the LCD backplane.
5	P1.2/FP25/ZX	General-Purpose Digital I/O Port 1.2/LCD Segment Output 25/ZX Output.
6	P1.3/T2EX/FP24	General-Purpose Digital I/O Port 1.3/Timer 2 Control Input/LCD Segment Output 24.
7	P1.4/T2/FP23	General-Purpose Digital I/O Port 1.4/Timer 2 Input/LCD Segment Output 23.
8	P1.5/FP22	General-Purpose Digital I/O Port 1.5/LCD Segment Output 22.
9	P1.6/FP21	General-Purpose Digital I/O Port 1.6/LCD Segment Output 21.
10	P1.7/FP20	General-Purpose Digital I/O Port 1.7/LCD Segment Output 20.
11	P0.1/FP19	General-Purpose Digital I/O Port 0.1/LCD Segment Output 19.
12	P2.0/FP18	General-Purpose Digital I/O Port 2.0/LCD Segment Output 18.
13	P2.1/FP17	General-Purpose Digital I/O Port 2.1/LCD Segment Output 17.
14	P2.2/FP16	General-Purpose Digital I/O Port 2.2/LCD Segment Output 16.
15	LCDVC	Output Port for LCD Levels. This pin should be decoupled with a 470 nF capacitor.
16	LCDVP2	Analog Output. A 100 nF capacitor should be connected between this pin and LCDVP1 for the internal LCD charge pump device.
17, 18	LCDVB, LCDVA	Output Ports for LCD Levels. These pins should be decoupled with a 470 nF capacitor.
19	LCDVP1	Analog Output. A 100 nF capacitor should be connected between this pin and LCDVP2 for the internal LCD charge pump device.
20 to 35	FP15 to FP0	LCD Segment Output 15 to LCD Segment Output 0.
36	P1.1/TxD	General-Purpose Digital I/O Port 1.1/Transmitter Data Output (Asynchronous).
37	P1.0/RxD	General-Purpose Digital I/O Port 1.0/Receive Data Input (Asynchronous).
38	P0.7/SS/T1/RxD2	General-Purpose Digital I/O Port 0.7/Slave Select When SPI Is in Slave Mode/Timer 1 Input/Receive Data Input 2 (Asynchronous).
39	P0.6/SCLK/T0	General-Purpose Digital I/O Port 0.6/Clock Output for I ² C or SPI Port/Timer 0 Input.
40	P0.5/MISO/ZX	General-Purpose Digital I/O Port 0.5/Data Input for SPI Port/ZX Output.
41	P0.4/MOSI/SDATA	General-Purpose Digital I/O Port 0.4/Data Output for SPI Port/I ² C-Compatible Data Line.

Pin No.	Mnemonic	Description
42	P0.3/CF2	General-Purpose Digital I/O Port 0.3/Calibration Frequency Logic Output 2. The CF2 logic output gives instantaneous active, reactive, or apparent power or I_{rms} information.
43	P0.2/CF1	General-Purpose Digital I/O Port 0.2/Calibration Frequency Logic Output 1. The CF1 logic output gives instantaneous active, reactive, or apparent power or I_{rms} information.
44	\overline{SDEN} /P2.3/TxD2	Serial Download Mode Enable/General-Purpose Digital Output Port 2.3/Transmitter Data Output 2 (Asynchronous). This pin is used to enable serial download mode through a resistor when pulled low on power-up or reset. On reset, this pin momentarily becomes an input, and the status of the pin is sampled. If there is no pull-down resistor in place, the pin momentarily goes high, and then user code is executed. If the pin is pulled down on reset, the embedded serial download/debug kernel executes, and this pin remains low during the internal program execution. After reset, this pin can be used as a digital output port pin (P2.3) or as Transmitter Data Output 2 (asynchronous).
45	BCTRL/ $\overline{INT1}$ /P0.0	Digital Input for Battery Control/External Interrupt Input 1/General-Purpose Digital I/O Port 0.0. This logic input connects V_{DD} or V_{BAT} to V_{SWOUT} internally when set to logic high or logic low, respectively. When left open, the connection between V_{DD} or V_{BAT} and V_{SWOUT} is selected internally.
46	XTAL2	A crystal can be connected across this pin and XTAL1 (see the XTAL1 pin description) to provide a clock source. The XTAL2 pin can drive one CMOS load when an external clock is supplied at XTAL1 or by the gate oscillator circuit. An internal 6 pF capacitor is connected to this pin.
47	XTAL1	An external clock can be provided at this logic input. Alternatively, a tuning fork crystal can be connected across XTAL1 and XTAL2 to provide a clock source. The clock frequency for specified operation is 32.768 kHz. An internal 6 pF capacitor is connected to this pin.
48	$\overline{INT0}$	External Interrupt Input 0.
49, 50	V_P, V_N	Analog Inputs for Voltage Channel. These inputs are fully differential voltage inputs with a maximum differential level of ± 500 mV for specified operation. This channel also has an internal PGA.
51	\overline{EA}	Input for Emulation. When held high, this input enables the device to fetch code from internal program memory locations. The ADE5166/ADE5169 do not support external code memory. This pin should not be left floating.
52, 53	I_{PA}, I_N	Analog Inputs for Current Channel. These inputs are fully differential voltage inputs with a maximum differential level of ± 500 mV for specified operation. This channel also has an internal PGA.
54	AGND	Ground Reference for Analog Circuitry.
55	I_{PB}	Analog Input for Second Current Channel. This input is fully differential with a maximum differential level of ± 500 mV, referred to I_N for specified operation. This channel also has an internal PGA.
56	\overline{RESET}	Reset Input, Active Low.
57	REF _{IN/OUT}	Access to On-Chip Voltage Reference. The on-chip reference has a nominal value of $1.2\text{ V} \pm 0.1\%$ and a typical temperature coefficient of 50 ppm/ $^{\circ}\text{C}$ maximum. This pin should be decoupled with a 1 μF capacitor in parallel with a ceramic 100 nF capacitor.
58	V_{BAT}	Power Supply Input from the Battery with a 2.4 V to 3.7 V Range. This pin is connected internally to V_{DD} when the battery is selected as the power supply.
59	V_{INTA}	Access to On-Chip 2.5 V Analog LDO. No external active circuitry should be connected to this pin. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
60	V_{DD}	3.3 V Power Supply Input from the Regulator. This pin is connected internally to V_{SWOUT} when the regulator is selected as the power supply. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
61	V_{SWOUT}	3.3 V Power Supply Output. This pin provides the supply voltage for the LDOs and the internal circuitry. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
62	V_{INTD}	Access to On-Chip 2.5 V Digital LDO. No external active circuitry should be connected to this pin. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
63	DGND	Ground Reference for Digital Circuitry.
64	V_{DCIN}	Analog Input for DC Voltage Monitoring. The maximum input voltage on this pin is V_{SWOUT} with respect to AGND. This pin is used to monitor the preregulated dc voltage.

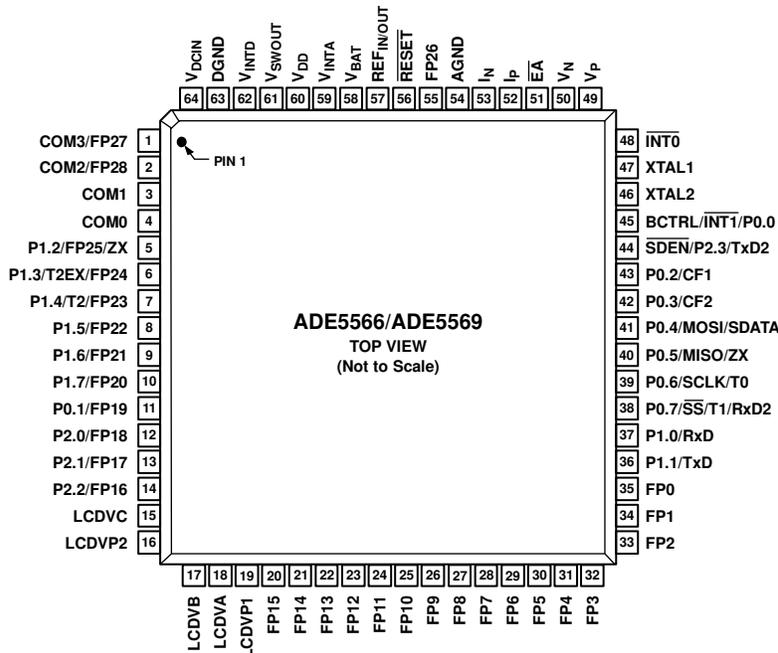


Figure 10. ADE5566/ADE5569 Pin Configuration

07411-028

Table 14. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	COM3/FP27	Common Output 3/LCD Segment Output 27. COM3 is used for the LCD backplane.
2	COM2/FP28	Common Output 2/LCD Segment Output 28. COM2 is used for the LCD backplane.
3	COM1	Common Output 1. COM1 is used for the LCD backplane.
4	COM0	Common Output 0. COM0 is used for the LCD backplane.
5	P1.2/FP25/ZX	General-Purpose Digital I/O Port 1.2/LCD Segment Output 25/ZX Output.
6	P1.3/T2EX/FP24	General-Purpose Digital I/O Port 1.3/Timer 2 Control Input/LCD Segment Output 24.
7	P1.4/T2/FP23	General-Purpose Digital I/O Port 1.4/Timer 2 Input/LCD Segment Output 23.
8	P1.5/FP22	General-Purpose Digital I/O Port 1.5/LCD Segment Output 22.
9	P1.6/FP21	General-Purpose Digital I/O Port 1.6/LCD Segment Output 21.
10	P1.7/FP20	General-Purpose Digital I/O Port 1.7/LCD Segment Output 20.
11	P0.1/FP19	General-Purpose Digital I/O Port 0.1/LCD Segment Output 19.
12	P2.0/FP18	General-Purpose Digital I/O Port 2.0/LCD Segment Output 18.
13	P2.1/FP17	General-Purpose Digital I/O Port 2.1/LCD Segment Output 17.
14	P2.2/FP16	General-Purpose Digital I/O Port 2.2/LCD Segment Output 16.
15	LCDVC	Output Port for LCD Levels. This pin should be decoupled with a 470 nF capacitor.
16	LCDVP2	Analog Output. A 100 nF capacitor should be connected between this pin and LCDVP1 for the internal LCD charge pump device.
17, 18	LCDVB, LCDVA	Output Ports for LCD Levels. These pins should be decoupled with a 470 nF capacitor.
19	LCDVP1	Analog Output. A 100 nF capacitor should be connected between this pin and LCDVP2 for the internal LCD charge pump device.
20 to 35	FP15 to FP0	LCD Segment Output 15 to LCD Segment Output 0.
36	P1.1/TxD	General-Purpose Digital I/O Port 1.1/Transmitter Data Output (Asynchronous).
37	P1.0/RxD	General-Purpose Digital I/O Port 1.0/Receive Data Input (Asynchronous).
38	P0.7/SS/T1/RxD2	General-Purpose Digital I/O Port 0.7/Slave Select When SPI Is in Slave Mode/Timer 1 Input/Receive Data Input 2 (Asynchronous).
39	P0.6/SCLK/T0	General-Purpose Digital I/O Port 0.6/Clock Output for I ² C or SPI Port/Timer 0 Input.
40	P0.5/MISO/ZX	General-Purpose Digital I/O Port 0.5/Data Input for SPI Port/ZX Output.
41	P0.4/MOSI/SDATA	General-Purpose Digital I/O Port 0.4/Data Output for SPI Port/I ² C-Compatible Data Line.
42	P0.3/CF2	General-Purpose Digital I/O Port 0.3/Calibration Frequency Logic Output 2. The CF2 logic output gives instantaneous active, reactive, or apparent power or I _{rms} information.

Pin No.	Mnemonic	Description
43	P0.2/CF1	General-Purpose Digital I/O Port 0.2/Calibration Frequency Logic Output 1. The CF1 logic output gives instantaneous active, reactive, or apparent power or I_{rms} information.
44	\overline{SDEN} /P2.3/TxD2	Serial Download Mode Enable/General-Purpose Digital Output Port 2.3/Transmitter Data Output 2 (Asynchronous). This pin is used to enable serial download mode through a resistor when pulled low on power-up or reset. On reset, this pin momentarily becomes an input, and the status of the pin is sampled. If there is no pull-down resistor in place, the pin momentarily goes high, and then user code is executed. If the pin is pulled down on reset, the embedded serial download/debug kernel executes, and this pin remains low during the internal program execution. After reset, this pin can be used as a digital output port pin (P2.3) or as Transmitter Data Output 2 (asynchronous).
45	BCTRL/ $\overline{INT1}$ /P0.0	Digital Input for Battery Control/External Interrupt Input 1/General-Purpose Digital I/O Port 0.0. This logic input connects V_{DD} or V_{BAT} to V_{SWOUT} internally when set to logic high or logic low, respectively. When left open, the connection between V_{DD} or V_{BAT} and V_{SWOUT} is selected internally.
46	XTAL2	A crystal can be connected across this pin and XTAL1 (see the XTAL1 pin description) to provide a clock source. The XTAL2 pin can drive one CMOS load when an external clock is supplied at XTAL1 or by the gate oscillator circuit. An internal 6 pF capacitor is connected to this pin.
47	XTAL1	An external clock can be provided at this logic input. Alternatively, a tuning fork crystal can be connected across XTAL1 and XTAL2 to provide a clock source. The clock frequency for specified operation is 32.768 kHz. An internal 6 pF capacitor is connected to this pin.
48	$\overline{INT0}$	External Interrupt Input 0.
49, 50	V_P, V_N	Analog Inputs for Voltage Channel. These inputs are fully differential voltage inputs with a maximum differential level of ± 500 mV for specified operation. This channel also has an internal PGA.
51	\overline{EA}	Input for Emulation. When held high, this input enables the device to fetch code from internal program memory locations. The ADE5566/ADE5569 do not support external code memory. This pin should not be left floating.
52, 53	I_P, I_N	Analog Inputs for Current Channel. These inputs are fully differential voltage inputs with a maximum differential level of ± 500 mV for specified operation. This channel also has an internal PGA.
54	AGND	Ground Reference for Analog Circuitry.
55	FP26	LCD Segment Output 26.
56	\overline{RESET}	Reset Input, Active Low.
57	REF _{IN/OUT}	Access to On-Chip Voltage Reference. The on-chip reference has a nominal value of $1.2\text{ V} \pm 0.1\%$ and a typical temperature coefficient of 50 ppm/°C maximum. This pin should be decoupled with a 1 μF capacitor in parallel with a ceramic 100 nF capacitor.
58	V_{BAT}	Power Supply Input from the Battery with a 2.4 V to 3.7 V Range. This pin is connected internally to V_{DD} when the battery is selected as the power supply.
59	V_{INTA}	Access to On-Chip 2.5 V Analog LDO. No external active circuitry should be connected to this pin. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
60	V_{DD}	3.3 V Power Supply Input from the Regulator. This pin is connected internally to V_{SWOUT} when the regulator is selected as the power supply. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
61	V_{SWOUT}	3.3 V Power Supply Output. This pin provides the supply voltage for the LDOs and the internal circuitry. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
62	V_{INTD}	Access to On-Chip 2.5 V Digital LDO. No external active circuitry should be connected to this pin. This pin should be decoupled with a 10 μF capacitor in parallel with a ceramic 100 nF capacitor.
63	DGND	Ground Reference for Digital Circuitry.
64	V_{DCIN}	Analog Input for DC Voltage Monitoring. The maximum input voltage on this pin is V_{SWOUT} with respect to AGND. This pin is used to monitor the preregulated dc voltage.

TYPICAL PERFORMANCE CHARACTERISTICS

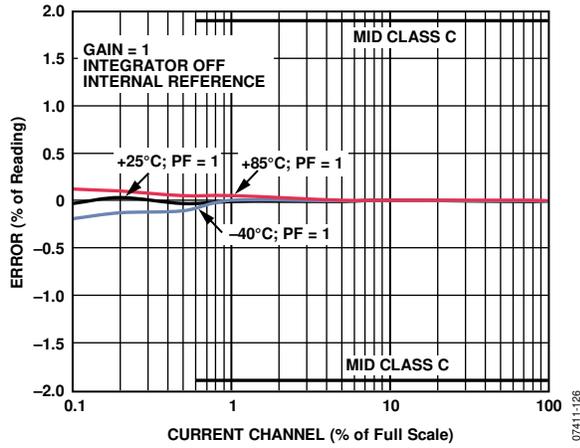


Figure 11. Active Energy Error as a Percentage of Reading (Gain = 1) over Temperature with Internal Reference, Integrator Off

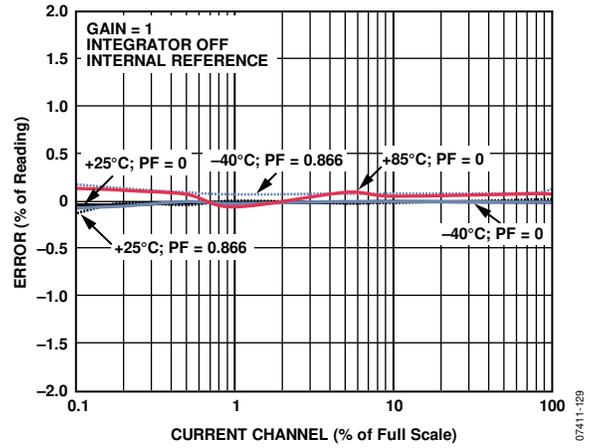


Figure 14. Reactive Energy Error as a Percentage of Reading (Gain = 1) over Power Factor with Internal Reference, Integrator Off

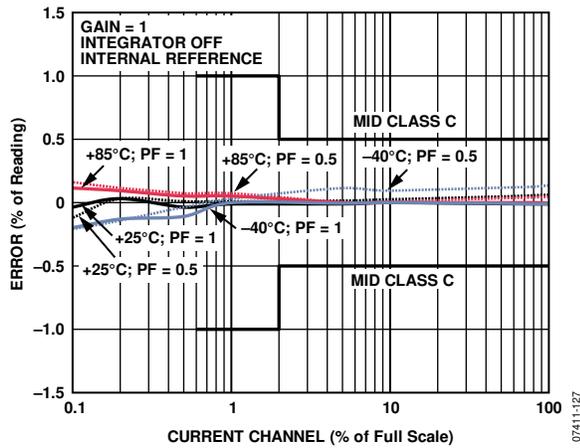


Figure 12. Active Energy Error as a Percentage of Reading (Gain = 1) over Power Factor with Internal Reference, Integrator Off

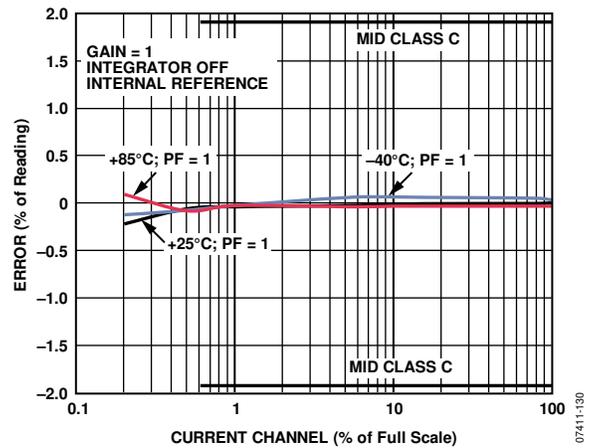


Figure 15. Current RMS Error as a Percentage of Reading (Gain = 1) over Temperature with Internal Reference, Integrator Off

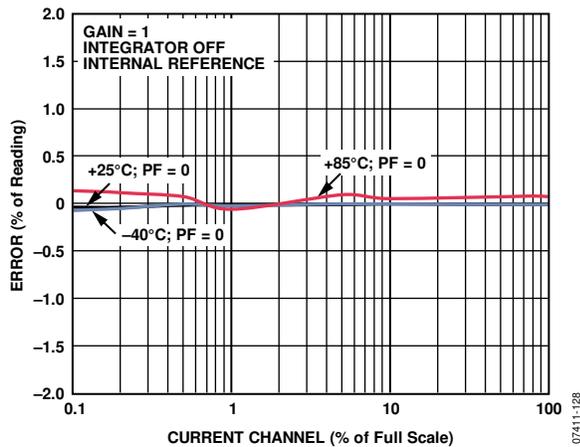


Figure 13. Reactive Energy Error as a Percentage of Reading (Gain = 1) over Temperature with Internal Reference, Integrator Off

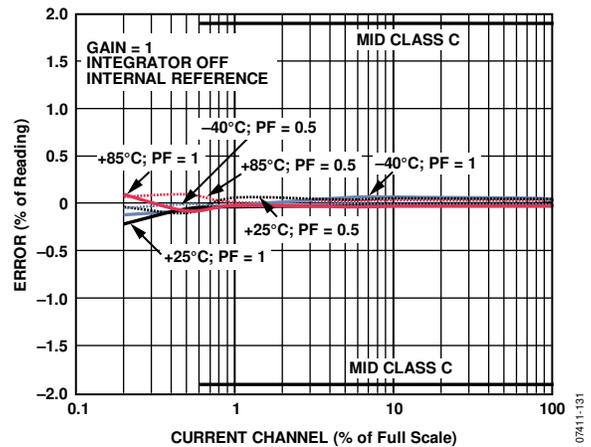


Figure 16. Current RMS Error as a Percentage of Reading (Gain = 1) over Power Factor with Internal Reference, Integrator Off

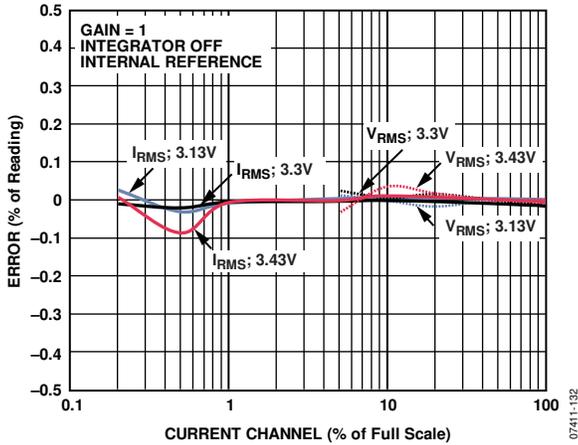


Figure 17. Voltage and Current RMS Error as a Percentage of Reading (Gain = 1) over Power Supply with Internal Reference

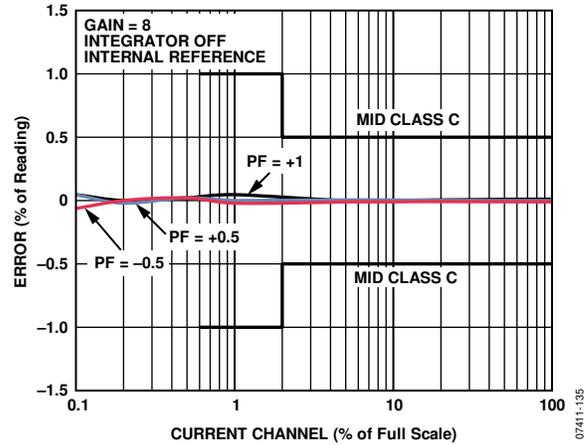


Figure 20. Active Energy Error as a Percentage of Reading (Gain = 8) over Power Factor with Internal Reference, Integrator Off

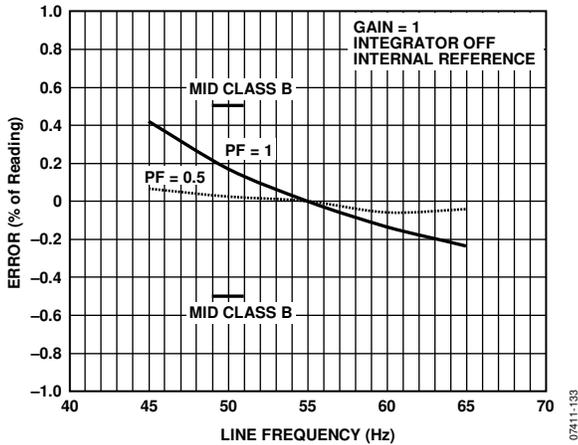


Figure 18. Active Energy Error as a Percentage of Reading (Gain = 1) over Frequency with Internal Reference, Integrator Off

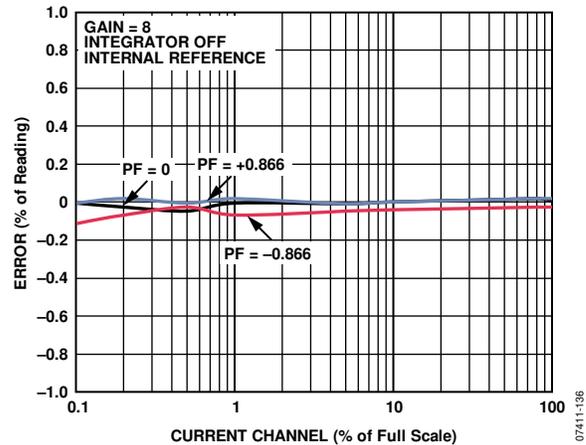


Figure 21. Reactive Energy Error as a Percentage of Reading (Gain = 8) over Power Factor with Internal Reference, Integrator Off

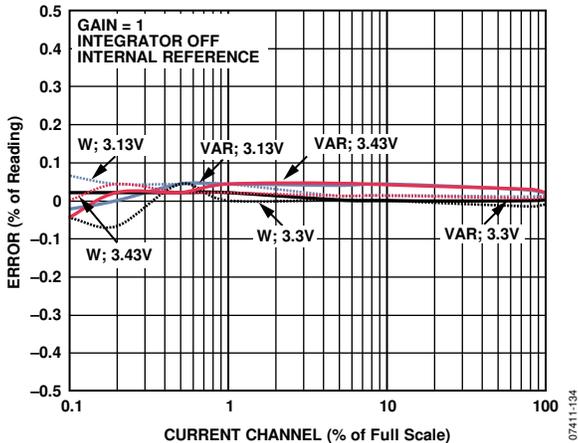


Figure 19. Active and Reactive Energy Error as a Percentage of Reading (Gain = 1) over Power Supply with Internal Reference, Integrator Off

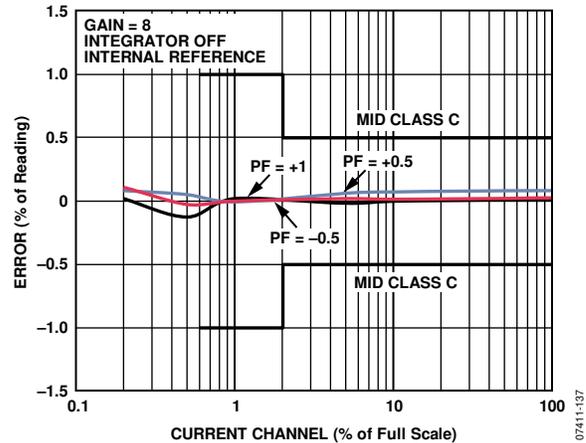


Figure 22. Current RMS Error as a Percentage of Reading (Gain = 8) over Power Factor with Internal Reference, Integrator Off

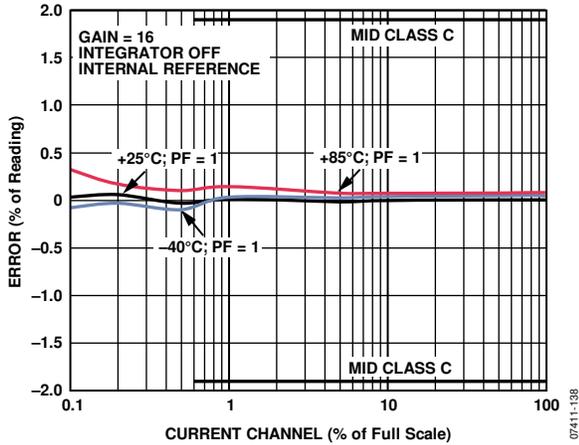


Figure 23. Active Energy Error as a Percentage of Reading (Gain = 16) over Temperature with Internal Reference, Integrator Off

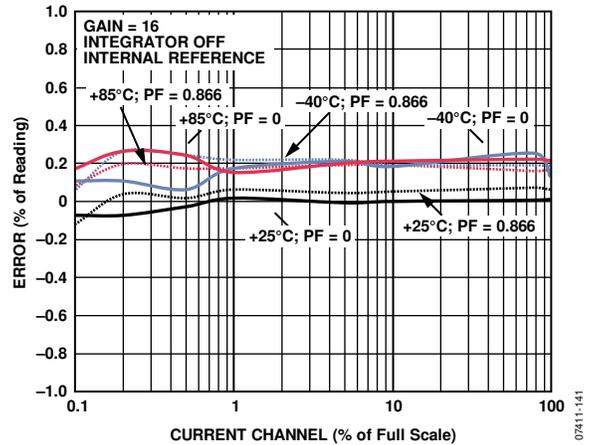


Figure 26. Reactive Energy Error as a Percentage of Reading (Gain = 16) over Power Factor with Internal Reference, Integrator Off

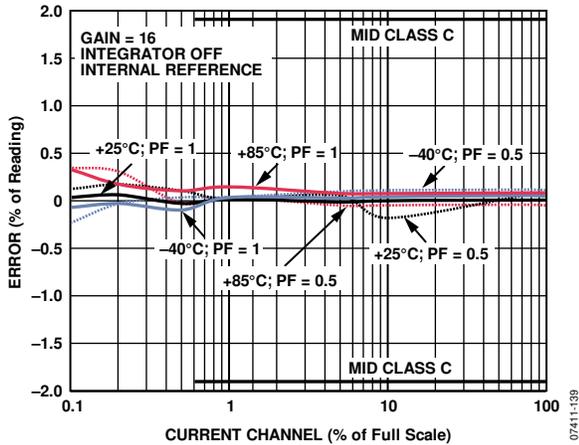


Figure 24. Active Energy Error as a Percentage of Reading (Gain = 16) over Power Factor with Internal Reference, Integrator Off

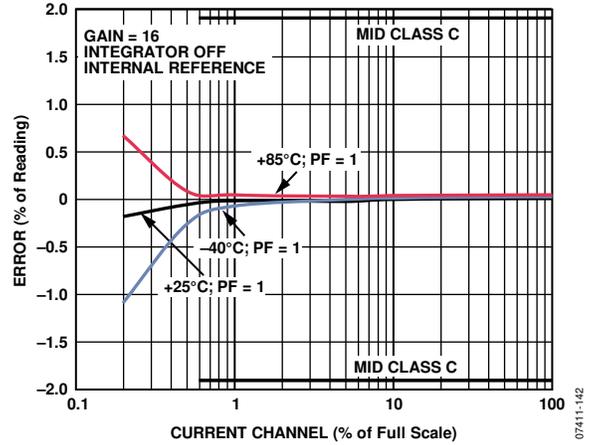


Figure 27. Current RMS Error as a Percentage of Reading (Gain = 16) over Temperature with Internal Reference, Integrator Off

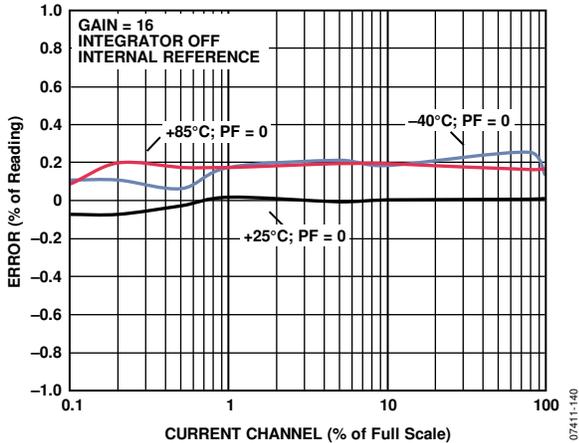


Figure 25. Reactive Energy Error as a Percentage of Reading (Gain = 16) over Temperature with Internal Reference, Integrator Off

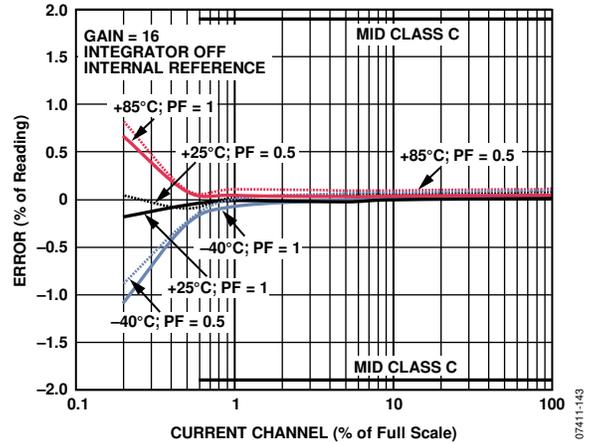


Figure 28. Current RMS Error as a Percentage of Reading (Gain = 16) over Power Factor with Internal Reference, Integrator Off

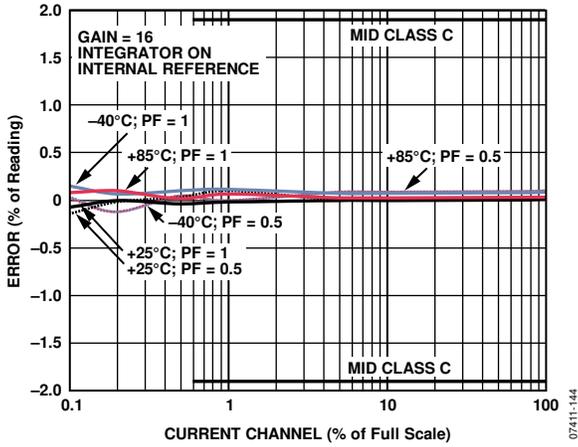


Figure 29. Active Energy Error as a Percentage of Reading (Gain = 16) over Power Factor with Internal Reference, Integrator On

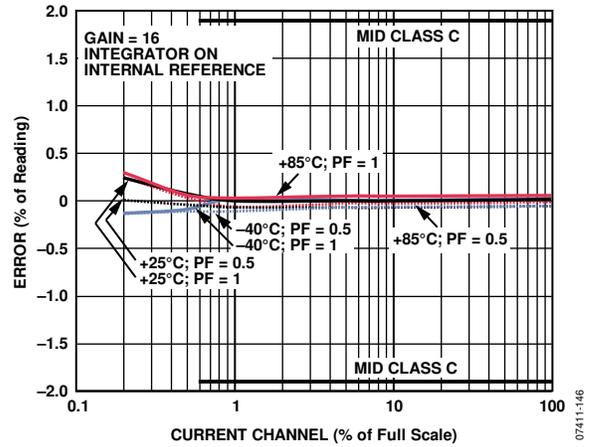


Figure 31. Current RMS Error as a Percentage of Reading (Gain = 16) over Power Factor with Internal Reference, Integrator On

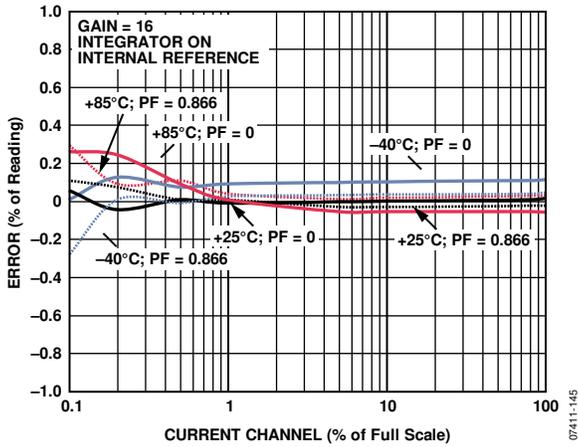


Figure 30. Reactive Energy Error as a Percentage of Reading (Gain = 16) over Power Factor with Internal Reference, Integrator On

TERMINOLOGY

Measurement Error

The error associated with the energy measurement made by the ADE5166/ADE5169/ADE5566/ADE5569 is defined by the following formula:

Measurement Error =

$$\left(\frac{\text{Energy Register} - \text{True Energy}}{\text{True Energy}} \right) \times 100\%$$

Phase Error Between Channels

The digital integrator and the high-pass filter (HPF) in the current channel have a nonideal phase response. To offset this phase response and equalize the phase response between channels, two phase correction networks are placed in the current channel: one for the digital integrator and the other for the HPF. The phase correction networks correct the phase response of the corresponding component and ensure a phase match between the current channel and the voltage channel to within $\pm 0.1^\circ$ over a range of 45 Hz to 65 Hz with the digital integrator off. With the digital integrator on, the phase is corrected to within $\pm 0.4^\circ$ over a range of 45 Hz to 65 Hz.

Power Supply Rejection (PSR)

PSR quantifies the ADE5166/ADE5169/ADE5566/ADE5569 measurement error as a percentage of reading when the power supplies are varied. For the ac PSR measurement, a reading at nominal supplies (3.3 V) is taken. A second reading is obtained

with the same input signal levels when an ac signal (100 mV rms/120 Hz) is introduced onto the supplies. Any error introduced by this ac signal is expressed as a percentage of the reading (see the Measurement Error definition).

For the dc PSR measurement, a reading at nominal supplies (3.3 V) is taken. A second reading is obtained with the same input signal levels when the supplies are varied $\pm 5\%$. Any error introduced is expressed as a percentage of the reading.

ADC Offset Error

ADC offset error is the dc offset associated with the analog inputs to the ADCs. It means that, with the analog inputs connected to AGND, the ADCs still see a dc analog input signal. The magnitude of the offset depends on the gain and input range selection. However, when HPF1 is switched on, the offset is removed from the current channel, and the power calculation is not affected by this offset. The offsets can be removed by performing an offset calibration (see the Analog Inputs section).

Gain Error

Gain error is the difference between the measured ADC output code (minus the offset) and the ideal output code (see the Current Channel ADC section and the Voltage Channel ADC section). It is measured for each of the gain settings on the current channel (1, 2, 4, 8, and 16). The difference is expressed as a percentage of the ideal code.